



DMN62D0UW

Product Summary

BV _{DSS}	Rds(on) max	I _D max T _A = +25°C
COV/	2Ω @ V _{GS} = 4.5V	340mA
60V	2.5Ω @ V _{GS} = 2.5V	300mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions
- Backlighting

N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

 An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMN62D0UWQ</u>)

Mechanical Data

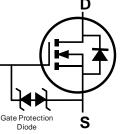
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.006 grams (Approximate)





SOT323 (Standard)

Top View



D G S

Equivalent Circuit



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN62D0UW-7	SOT323 (Standard)	3,000/Tape & Reel
DMN62D0UW-13	SOT323 (Standard)	10,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

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2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

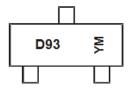
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Notes:



Marking Information



D93= Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2016		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	D		_	J	K	L	М	Ν	0	Р	R	S
Month	lan	Feb	Mor	A	Mari		L.J.	A	Com	0.04	Mari	Dee
wonth	Jan	гер	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit			
Drain-Source Voltage	V _{DSS}	60	V			
Gate-Source Voltage			Vgss	±20	V	
	Steady State	T _A = +25°C T _A = +70°C	ID	340 270	mA	
Continuous Drain Current (Note 6) VGS = 4.5V	t<5s	T _A = +25°C T _A = +70°C	lo	400 300	mA	
Maximum Continuous Body Diode Forward Currer	ls	340	mA			
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			ldм	1.2	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	320	mW
Thermal Desistance, Junction to Ambient (Note 5)	Steady State	Devi	398	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	Reja	306	C/W
Total Power Dissipation (Note 6)		PD	470	mW
Thermal Desistance, Junction to Ambient (Note 6)	Steady State	Devi	273	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	Reja	235	C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.



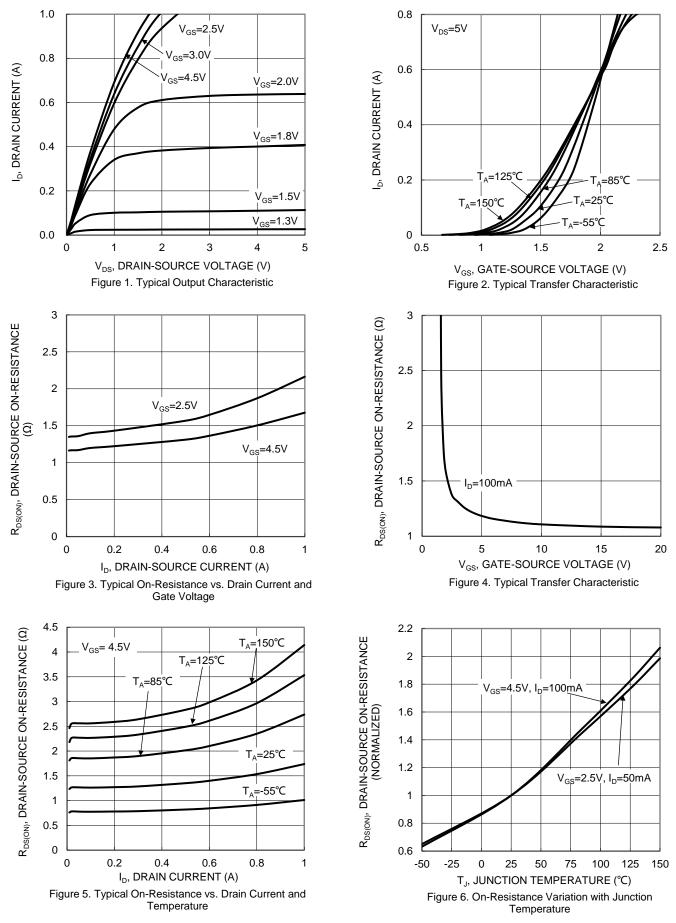
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			1			1
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			-			
Drain-Source Breakdown Voltage	BVDSS	60		_	V	$V_{GS} = 0V$, $I_D = 10\mu A$
Zero Gate Voltage Drain Current	IDSS			1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	Igss			±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(th)	0.5	_	1.0	V	V _{DS} = 10V, I _D = 250µA
			1.2	2.0		V _{GS} = 4.5V, I _D = 0.1A
Static Drain-Source On-Resistance	RDS(ON)		1.4	2.5	Ω	V _{GS} = 2.5V, I _D = 0.05A
			1.8	3.0		$V_{GS} = 1.8V, I_D = 0.05A$
Forward Transconductance	Yfs	_	1.8		s	V _{DS} =10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	32	-	pF	
Output Capacitance	Coss		3.9		рF	Vps = 30V, Vgs = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		2.4		рF	1 = 1.000112
Gate Resistance	Rg	_	101	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg		0.5		nC	
Gate-Source Charge	Qgs	_	0.09	_	nC	Vgs = 4.5V, Vps = 10V, Ip = 250mA
Gate-Drain Charge	Q _{gd}	_	0.09	—	nC	ID = 25011A
Turn-On Delay Time	tD(ON)		2.4	_	ns	
Turn-On Rise Time	tR		2.5		ns	V _{DD} = 30V, V _{GS} = 10V,
Turn-Off Delay Time	tD(OFF)		22.6	_	ns	$R_{G} = 25\Omega, I_{D} = 200 \text{mA}$
Turn-Off Fall Time	tF	_	12.5	-	ns	

7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing. Notes:

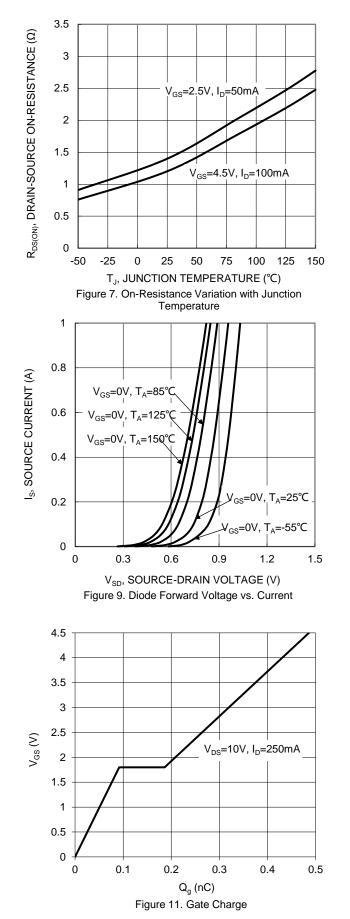


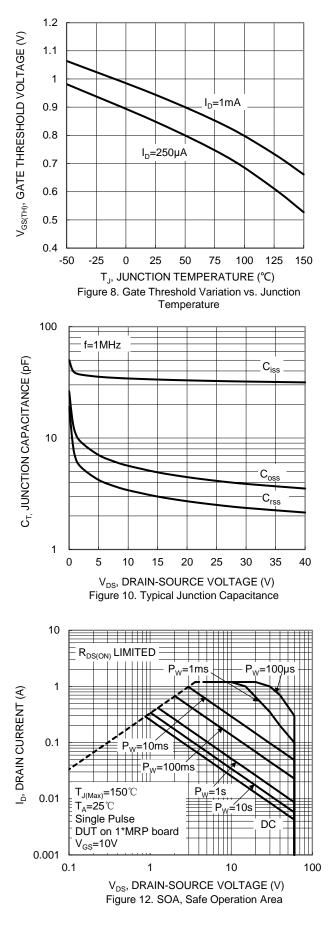
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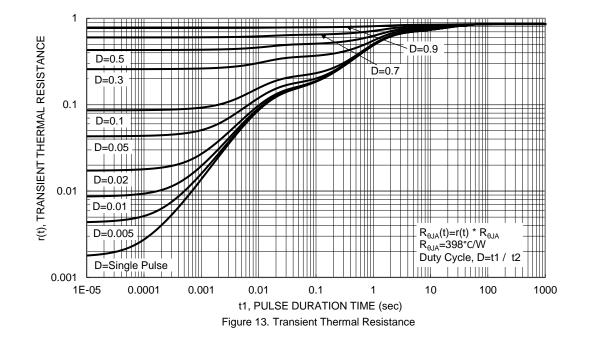
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5 of 8 Downloaded From Oneyac.com



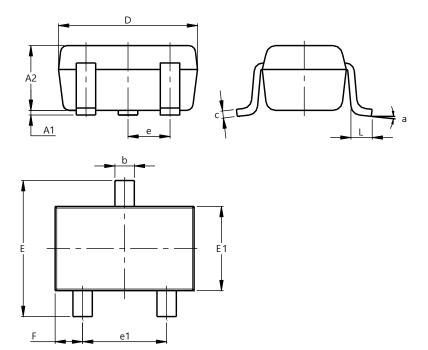




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323 (Standard)

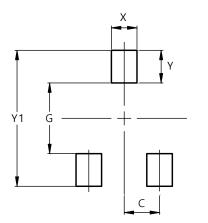


S	SOT323 (Standard)									
Dim	Min	Max	Тур							
A1	0.00	0.10	0.05							
A2	0.80	1.00	0.90							
b	0.20	0.40	0.30							
С	0.08	0.18	0.13							
D	1.80	2.20	2.00							
Е	2.00	2.45	2.225							
E1	1.15	1.35	1.25							
е	1		0.65							
e1	1.20	1.40	1.30							
F	0.25	0.475	0.3625							
L	0.25	0.46	0.355							
а	0°	8°								
All	All Dimensions in mm									

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323 (Standard)



Dimensions	Value (in mm)
С	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500



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